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PHASE CONTROL SCR

| | |
|---|--|
|  | $V_T < 1.45V @ 40A$ $I_{TSM} = 500A$ $V_{RRM} = 800 - 1200V$ |
|---|--|

Description/ Features

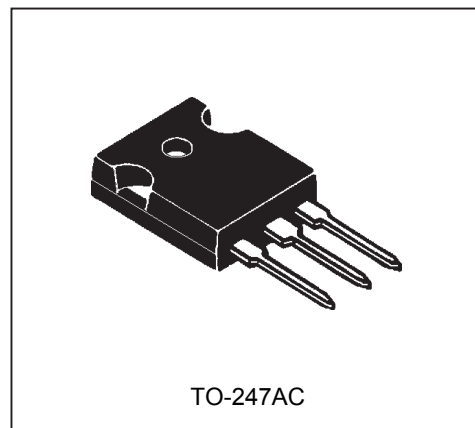
The 40TPS... **SAFEIR** series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125°C junction temperature. Low lgt parts available.

Typical applications are in input rectification (soft start) and these products are designed to be used with International Rectifier input diodes, switches and output rectifiers which are available in identical package outlines.

Major Ratings and Characteristics

| Characteristics | 40TPS.. | Units |
|----------------------------------|------------|------------|
| $I_{T(AV)}$ Sinusoidal waveform | 35 | A |
| I_{RMS} | 55 | A |
| V_{RRM}/V_{DRM} Range | 800 - 1200 | V |
| I_{TSM} | 500 | A |
| V_T @ 40 A, $T_J = 25^\circ C$ | 1.45 | V |
| dv/dt | 1000 | V/ μs |
| di/dt | 100 | A/ μs |
| T_J | -40 to 125 | $^\circ C$ |

Package Outline



Voltage Ratings

| Part Number | V_{RRM}/V_{DRM} , max. repetitive peak and off-state voltage V | V_{RSM} , maximum non repetitive peak reverse voltage V | I_{RRM}/I_{DRM} 125°C mA |
|-------------|---|--|----------------------------------|
| 40TPS08 | 800 | 900 | 10 |
| 40TPS12 | 1200 | 1300 | |

Absolute Maximum Ratings

| Parameters | 40TPS.. | Units | Conditions | |
|--|-----------|-------------------|---|---|
| $I_{T(AV)}$ Max. Average On-state Current | 35 | A | @ $T_C = 79^\circ\text{C}$, 180° conduction half sine wave | |
| $I_{T(RMS)}$ Max. Continuous RMS On-state Current As AC switch | 55 | | | |
| I_{TSM} Max. Peak One Cycle Non-Repetitive Surge Current | 500 | A | 10ms Sine pulse, rated V_{RRM} applied | Initial $T_J = T_J \text{ max.}$ |
| | 600 | | 10ms Sine pulse, no voltage reapplied | |
| I^2t Max. I^2t for Fusing | 1250 | A ² s | 10ms Sine pulse, rated V_{RRM} applied | |
| | 1760 | | 10ms Sine pulse, no voltage reapplied | |
| $I^2\sqrt{t}$ Max. $I^2\sqrt{t}$ for Fusing | 12500 | A ² √s | t = 0.1 to 10ms, no voltage reapplied | |
| $V_{T(TO)1}$ Low Level Value of Threshold Voltage | 1.02 | V | $T_J = 125^\circ\text{C}$ | |
| $V_{T(TO)2}$ High Level Value of Threshold Voltage | 1.23 | | | |
| r_{t1} Low Level Value of On-state Slope Resistance | 9.74 | mΩ | | |
| r_{t2} High Level Value of On-state Slope Resistance | 7.50 | | | |
| V_{TM} Max. Peak On-state Voltage | 1.85 | V | @ 110A, $T_J = 25^\circ\text{C}$ | |
| di/dt Max. Rate of Rise of Turned-on Current | 100 | A/μs | $T_J = 25^\circ\text{C}$ | |
| I_H Max. Holding Current | 150 | mA | | |
| I_L Max. Latching Current | 300 | | | |
| I_{RRM}/I_{DRM} Max. Reverse and Direct Leakage Current | 0.5 10 | mA | $T_J = 25^\circ\text{C}$ | $V_R = \text{rated } V_{RRM}/V_{DRM}$ |
| | | | $T_J = 125^\circ\text{C}$ | |
| dv/dt Max. Rate of Rise of Off-state Voltage | 40TPS08 | 500 | V/μs | $T_J = T_J \text{ max.}, \text{ linear to } 80\% V_{DRM}, R_g\text{-k} = \text{open}$ |
| | 40TPS12 | 1000 | | |

Triggering

| Parameters | 40TPS.. | Units | Conditions | |
|---|---------|-------|--|-------------------------------------|
| P_{GM} Max. peak Gate Power | 10 | W | | |
| $P_{G(AV)}$ Max. average Gate Power | 2.5 | | | |
| I_{GM} Max. peak Gate Current | 2.5 | A | | |
| $-V_{GM}$ Max. peak negative Gate Voltage | 10 | V | $T_J = -40^{\circ}\text{C}$ | Anode supply = 6V resistive load |
| V_{GT} Max. required DC Gate Voltage to trigger | 4.0 | | $T_J = 25^{\circ}\text{C}$ | |
| | 2.5 | | $T_J = 125^{\circ}\text{C}$ | |
| | 1.7 | | | |
| I_{GT} Max. required DC Gate Current to trigger | 270 | mA | $T_J = -40^{\circ}\text{C}$ | |
| | 150 | | $T_J = 25^{\circ}\text{C}$ | |
| | 80 | | $T_J = 125^{\circ}\text{C}$ | |
| | 40 | | $T_J = 25^{\circ}\text{C}$, for 40TPS08A and 40TPS12A | |
| V_{GD} Max. DC Gate Voltage not to trigger | 0.25 | V | $T_J = 125^{\circ}\text{C}$, V_{DRM} = rated value | |
| I_{GD} Max. DC Gate Current not to trigger | 6 | mA | | |

Thermal-Mechanical Specifications

| Parameters | 40TPS.. | Units | Conditions | |
|--|-------------|---------|--------------------------------------|--|
| T_J Max. Junction Temperature Range | - 40 to 125 | °C | | |
| T_{stg} Max. Storage Temperature Range | - 40 to 125 | | | |
| R_{thJC} Max. Thermal Resistance Junction to Case | 0.6 | °C/W | DC operation | |
| R_{thJA} Max. Thermal Resistance Junction to Ambient | 40 | | | |
| R_{thCS} Max. Thermal Resistance Case to Heatsink | 0.2 | | Mounting surface, smooth and greased | |
| wt Approximate Weight | 6 (0.21) | g (oz.) | | |
| T Mounting Torque | Min. | 6 (5) | Kg-cm (lbf-in) | |
| | Max. | 12 (10) | | |
| Case Style | TO-247AC | | | |

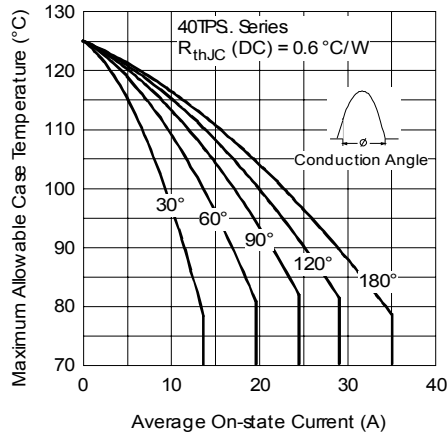


Fig. 1 - Current Rating Characteristics

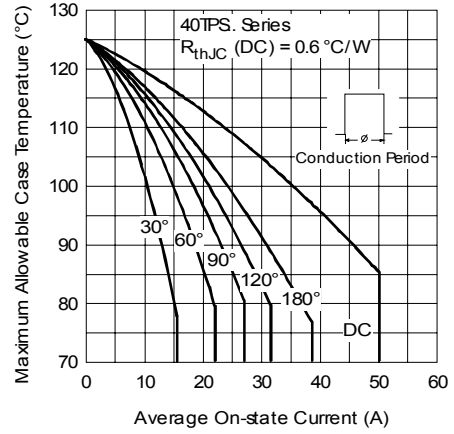


Fig. 2 - Current Rating Characteristics

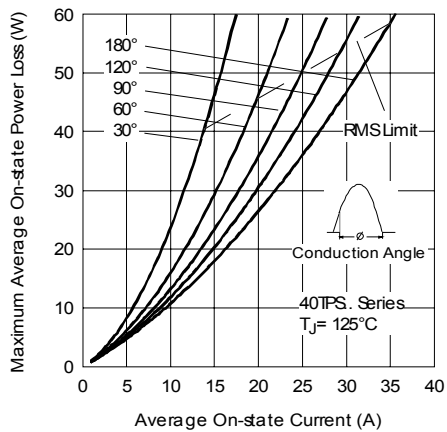


Fig. 3 - On-state Power Loss Characteristics

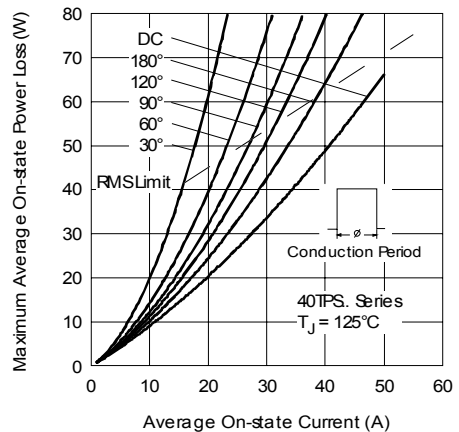


Fig. 4 - On-state Power Loss Characteristics

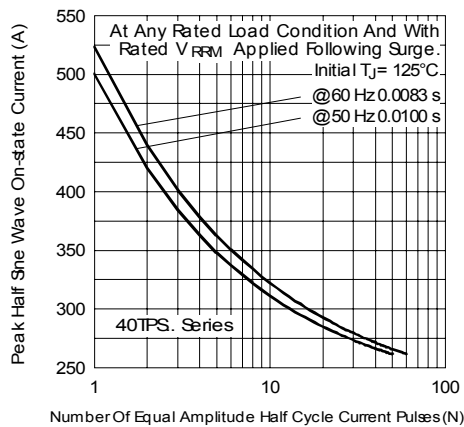


Fig. 5 - Maximum Non-Repetitive Surge Current

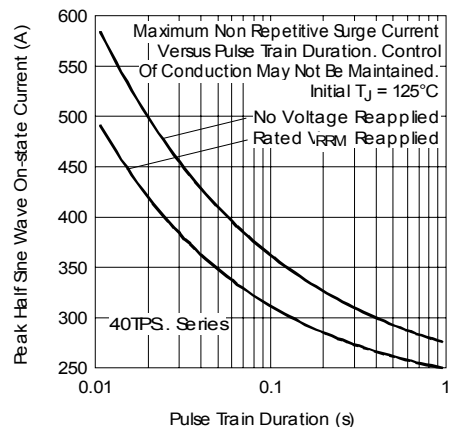


Fig. 6 - Maximum Non-Repetitive Surge Current

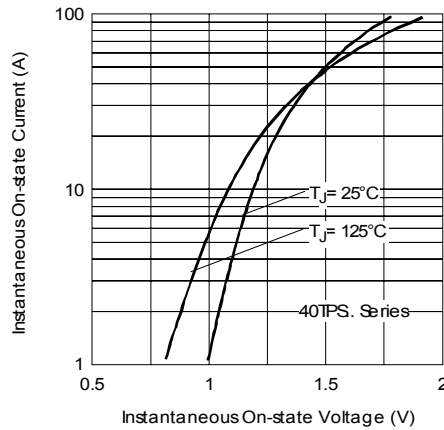


Fig. 7 - On-state Voltage Drop Characteristics

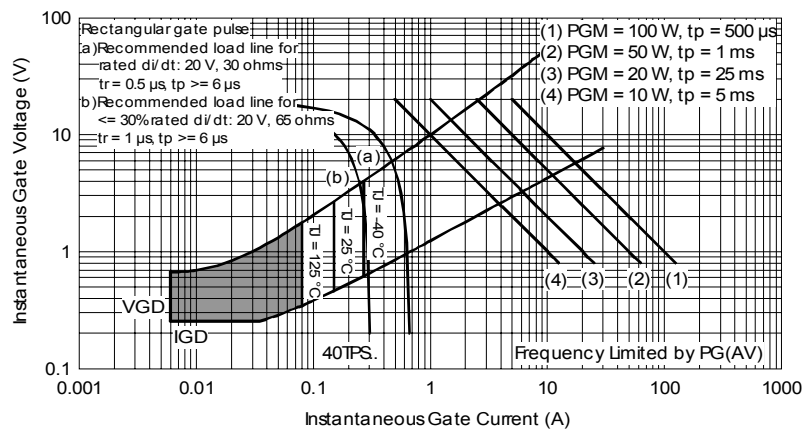


Fig. 8 - Gate Characteristics

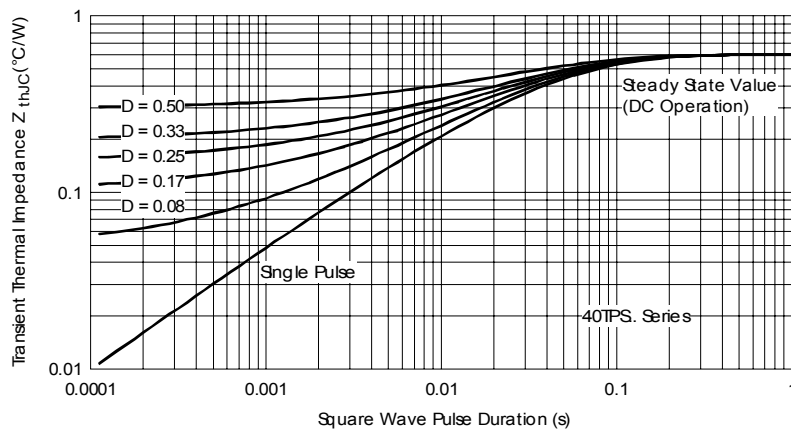
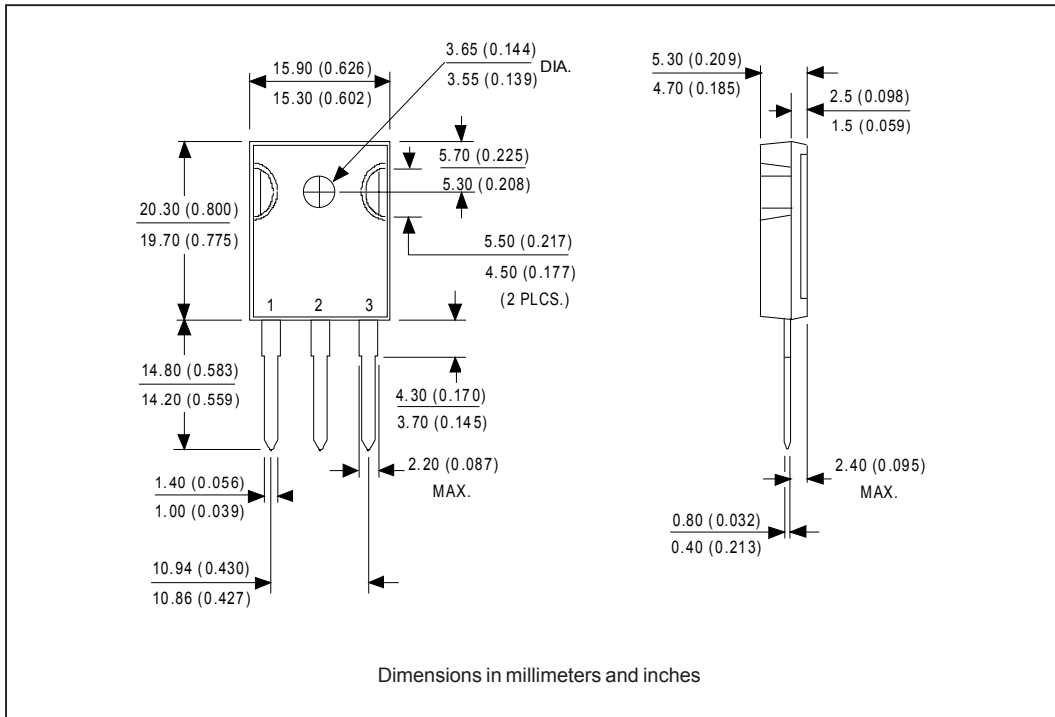
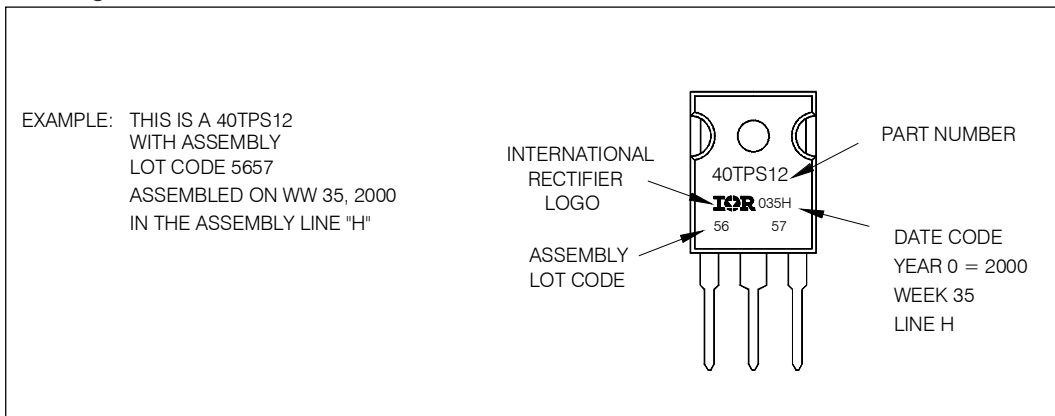


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

Outline Table



Marking Information



Ordering Information Table

| Device Code | | | | | |
|-------------|---|---|---|----|---|
| 40 | T | P | S | 12 | |
| ① | ② | ③ | ④ | ⑤ | ⑥ |

| | | | | |
|--|--|--|-----------|------------|
| <p>1 - Current Rating</p> <p>2 - Circuit Configuration: T = Thyristor</p> <p>3 - Package: P = TO-247</p> <p>4 - Type of Silicon: S = Standard Recovery Rectifier</p> <p>5 - Voltage code: Code x 100 = V_{RRM}</p> <p>6 - None = Standard Igt selection A = Low Igt selection 40mA max. for 40TPS08A and 40TPS12A</p> | | <table border="1"> <tr> <td>08 = 800V</td> </tr> <tr> <td>12 = 1200V</td> </tr> </table> | 08 = 800V | 12 = 1200V |
| 08 = 800V | | | | |
| 12 = 1200V | | | | |

Data and specifications subject to change without notice.
 This product has been designed and qualified for Industrial Level.
 Qualification Standards can be found on IR's Web site.